Contribution ID: **17** Type: **Standard (20 min including discussion)**

Study of irradiated NinN production and LGAD dopping profiles

Tuesday 23 June 2015 10:00 (20 minutes)

Trough SiMS measurements, the evolution of the doping profile is been studied for irradiated NinN samples at fluences of 10e15neq/cm2, while the transient current technique is used on diodes of the same implantation profile n order to evaluate the electrical characteristics evolution as a function of the received dose. Comparison and conclusions are established with the non-irradiated case both for the profile evolution and the intrinsic characteristics of the samples. A SiMS vs process simulation approach is used to model and control the new LGAD production in an attempt to understand post irradiation behavior and electrical characteristic.

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